Attorney Docket No. 0756-2330



IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re Patent Application of:) Group Art Unit: 2823	
Shunpei YAMAZAKI et al.) Examiner: B. Kebede	
Serial N o. 09/894,125) <u>CERTIFICATE OF MA</u> I hereby certify that this correspo	
Filed: June 29, 2001	deposited with the United States with sufficient postage as First C	Postal Service
For: CRYSTALLINE SEMICONDUCTOR	envelope addressed to: Commissi P.O. Box 1450, Alexandria, VA	oner for Patents,
THIN FILM, METHOD OF) 2.17.2604	22313 1130, 011
FABRICATING THE SAME,) add M Stamper	
SEMICONDUCTOR DEVICE, AND)	
METHOD OF FABRICATING THE)	
SAME)	

INFORMATION DISCLOSURE STATEMENT

Honorable Commissioner of Patents

P.O. Box 1450

Alexandria, VA 22313-1450

Sir:

In accordance with the provisions of 37 C.F.R. 1.56 and 37 C.F.R. 1.97-1.99, Applicant submits herewith a Form PTO-1449 listing references known to Applicant and requests that these references be made of record in the above identified application. Copies of the references listed are submitted herewith in accordance with 37 C.F.R. 1.98(a).

This Information Disclosure Statement is being submitted with an RCE. Therefore, no fee is required.

The Commissioner is hereby authorized to charge fees under 37 C.F.R. §§1.16, 1.17, 1.20(a), 1.20(b), 1.20(c), and 1.20(d) (except the Issue Fee) which may be

required now or hereafter, or credit any overpayment to Deposit Account No. 50-2280. A duplicate copy of this sheet is attached.

Respectfully submitted,

Eric J. Robinson

Reg. No. 38,285

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U.S. Patent and Trademark Office: U.S. DEPARTMENT OF COMMERCE of 1995, no persons are required to respond to a collection of information unless it contains a valid OMB control number.

Complete if Known 09/894,125 **Application Number** HON DISCLOSURE June 29, 2001 Filing Date STATEMENT BY APPLICANT Shunpei YAMAZAKI et al. First Named Inventor (use as many sheets as necessary) 2823 Group Art Unit B. Kebede Examiner Name Sheet ı of 1 Attorney Docket Number 0756-2330

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Examiner Initials*	Cite No.1	U.S. Patent Document		Name of Patentee or Applicant of Cited	Date of Publication of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear
			nd Code ² known)	Document	MM-DD-YYYY	
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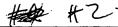
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¹Unique citation designation number. ² Applicant is to place a check mark here if English language Translation is attached.



Substitute for form 1449 A/PTO nplete if Known NEORMATION DISCLOSURE STATEMENT Application Number June 29, 2001 Filing Date BY APPLICANT First Named Inventor Shunpei YAMAZAKI et al. as many sheets as necessary) Group Art Unit 2823 Examiner Name B. Kebede Attorney Docket Number 740756-2330 U.S. PATENT DOCUMENTS Date of Publication of Cited U.S. Patent Document Pages, Columns, Lines, Where Relevant Cite No.1 Name of Patentee or Applicant of Cited Document MM-DD-YYYY Passages or Relevant Figures Appear Document Kind Code² (if known) Number 5,147,826 09/15/1992 Liu et al. 5,461,250 Burghartz et al. 10/24/1995 4,986,213 Yamazaki et al. 01/22/1991 6,124,154 Miyasaka 09/26/2000 5,403,772 04/04/1995 Zhang et al. 5,426,064 06/20/1995 Zhang et al. 5,639,698 Yamazaki et al. 06/17/1997 5,843,833 Ohtani et al. 12/01/1998 5,994,172 Ohtani et al. 11/30/1999 5,879,977 Zhang et al. 03/09/1999 6,140,165 Zhang et al. 10/31/2000 6,096,581 Zhang et al. 08/01/2000 6,054,739 Yamazaki et al. 04/25/2000 6,027,960 Kusumoto et al. 02/22/2000 FOREIGN PATENT DOCUMENTS Cite No. Foreign Patent Document Date of Publication of Cited Pages, Columns, Lines, Name of Patentee or Document MM-DD-YYYY Where Relevant Passages or Relevant Figures Appear Initials Kind Code Applicant of Cited Document Office3 (if known) OTHER PRIOR ART - NON PATENT LITERATURE DOCUMENTS Examiner Cite Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the T^2 Initials item (book, magazine, journal, serial, symposium, catalog, etc.)., date, page(s), volume-issue number(s), publisher, city and/or country where published. Dorin et al., "Chemistry The Study of Matter", 1992, pp. 532, Prentice Hall Aya et al., "Improvement of SPC poly-Si Film Using the ELA Method", September 11-12, 1997, pp. 167-170, AM-LCD. Abe et al., High-Performance Poly-Crystalline Silicon TFT's Fabricated Using the SPC and ELA Methods", July 9-10, 1998, pp. 85-88, AM-LCD. "Thresholds antiferroelectricity in liquid crystals and its application to displays", S. Inui et al., J. Mater. Chem., 6 (4), pages 6/1-673, 1996. U.S. Patent Application Serial No. 09/369,158 "Semiconductor Device and Method of Manufacturing the BK Same". U.S. Patent Application Serial No. 09/352,194 "Crystalline Semiconductor Thin Film, Method of Fabricating the Same Semiconductor Device, and Method of Fabricating the Same". BN Examiner Kehede BNOU 40m/20,2002 Signature Considered